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Sheet 1 of 1 FORM PTO-1449 (SUBSTITUTE) Attorney Docket No.: Applic. No. EHF 2001,0167 P 09/873,230 J.S. DEPARTMENT OF COMMERCE ATENT AND TRADEMARK OFFICE **Applicant** Norbert Benesch et al. INFORMATION DISCLOSURE STATEMENT BY APPLICANT Filing Date **Group Art Unit** (37 CFR 1.98(b)) June 4, 2001 2621 **U.S. PATENT DOCUMENTS** EXAMINER SUB FILING INITIALS PATENT NO. DATE **PATENTEE CLASS CLASS** DATE A В RECEIVED С D MAY 1'2 2004 Ε Technology Center 2600 F G Н **FOREIGN PATENT DOCUMENT** SUB TRANSL. DOCUMENT NO. DATE COUNTRY **CLASS CLASS** YES I NO JS J 61 169 750 07/31/86 Japan Х Κ 15 62 200 251 09/03/87 Japan Х 15 L 9 191 032 07/22/97 Japan X 15 9 3 1 8 3 3 0 12/12/97 Japan Х Ν OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.) **EXAMINER** DATE CONSIDERED 6/16/04 EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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